

EE 40 – Introduction to Microelectronic Circuits

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Course Web Site

<http://www-inst.eecs.berkeley.edu/~ee40/>**Problem Set # 10****Due: 5 PM Tuesday, Nov. 15th, 2005 in 240 Cory****10.1 MOS Physics**

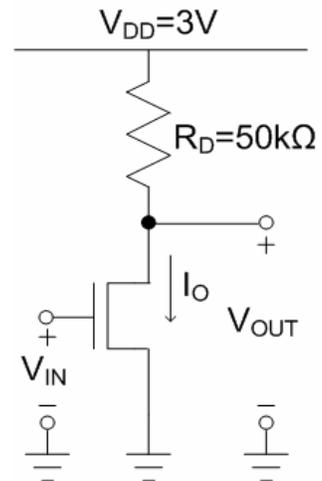
An NMOS device produces a current of $50 \mu\text{A}$ when operated at $V_{GS}=3\text{V}$ and $V_{DS}=3\text{V}$. The device has $W/L=2$, $V_T=1\text{V}$, and p-substrate doping $N_A=10^{16} \text{ cm}^{-3}$. The electric permittivity of Silicon dioxide is about $\epsilon_{ox}=3.9*\epsilon_0$, where ϵ_0 is the electric permittivity of free space.

- Find the device parameters μ_n , C_{ox} , and t_{ox} , assuming a pinch-off saturation behavior.
- Find the device parameters μ_n , C_{ox} , and t_{ox} , assuming a velocity saturation behavior with $V_{DSAT}=1.5\text{V}$.
- Compare the current in the two devices from parts (a) and (b) when operated at $V_{GS}=1.5\text{V}$ and $V_{DS}=3\text{V}$. (Hint: Remember that MOSFET current saturates for $V_{DS} \geq \min(V_{GS}-V_T, V_{DSAT})$, where $V_{GS}-V_T$ is the condition for pinch-off and V_{DSAT} is the condition for velocity saturation.)

10.2 NMOS Inverter

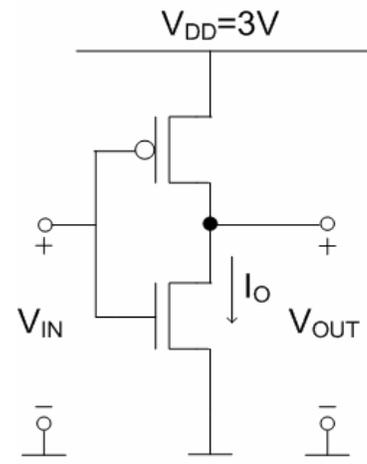
For the circuit shown in Figure 1, answer the following questions, using the NMOS_4XVS model given in Lecture 27.

- Plot I_O vs. V_{OUT} for both the pull-up and pull-down devices for $V_{IN} = 1\text{V}$, 2V , and 3V .
- Plot the voltage transfer characteristic (VTC), V_{OUT} vs. V_{IN} . What is the minimum V_{OUT} for this inverter? How can you change R_D to lower this value?
- Find the power in the pull-up and pull-down devices when $V_{IN}=0\text{V}$ and $V_{IN}=3\text{V}$.

**Figure 1 – NMOS Inverter****10.3 CMOS Inverter**

For the circuit shown in Figure 2, answer the following questions, using the NMOS_4XVS model given in Lecture 27 and the PMOS_4XVS model given in Lecture 28.

- Plot I_O vs. V_{OUT} for both the pull-up and pull-down devices for $V_{IN} = 1\text{V}$, 1.25V , 1.5V , 1.75V , and 2V .
- Plot the voltage transfer characteristic (VTC), V_{OUT} vs. V_{IN} . What is output voltage range for this inverter?
- Find the power in the pull-up and pull-down devices when $V_{IN}=0\text{V}$ and $V_{IN}=3\text{V}$. How does the power consumption of the CMOS inverter compare to the NMOS inverter?

**Figure 2 – CMOS Inverter**